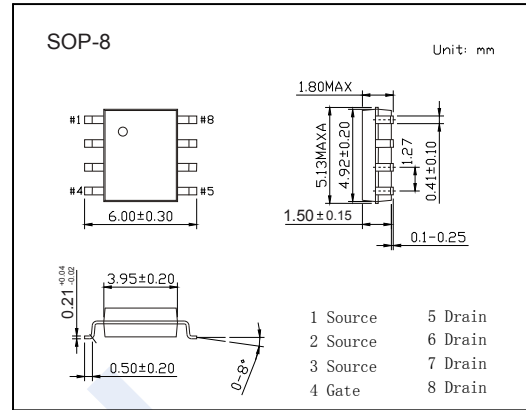
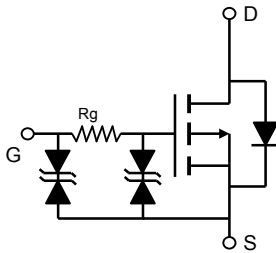


P-Channel MOSFET

AO4447A (KO4447A)

■ Features

- $V_{DS} (V) = -30V$
- $I_D = -17 A (V_{GS} = -10V)$
- $R_{DS(ON)} < 7m\Omega (V_{GS} = -10V)$
- $R_{DS(ON)} < 8m\Omega (V_{GS} = -4.5V)$
- $R_{DS(ON)} < 9m\Omega (V_{GS} = -4V)$
- ESD Rating: 2000V HBM



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	-30	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	I_D	$T_A = 25^\circ C$	-17	A
		$T_A = 70^\circ C$	-13	
Pulsed Drain Current	I_{DM}	-160		
Power Dissipation	P_D	$T_A = 25^\circ C$	3.1	W
		$T_A = 70^\circ C$	2	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	40	$^\circ C/W$
		Steady-State	75	
Thermal Resistance.Junction- to-Lead	R_{thJL}	24		
Junction Temperature	T_J	150	$^\circ C$	
Junction Storage Temperature Range	T_{stg}	-55 to 150		

P-Channel MOSFET

AO4447A (KO4447A)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μA, V _{GS} =0V	-30			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA	
		V _{DS} =-30V, V _{GS} =0V, T _J =55°C			-5		
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±16V			±10	μA	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.8		-1.6	V	
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-17A			7	mΩ	
		V _{GS} =-10V, I _D =-17A T _J =125°C			8.5		
		V _{GS} =-4.5V, I _D =-15A			8		
		V _{GS} =-4V, I _D =-13A			9		
On state drain current	I _{D(ON)}	V _{GS} =-10V, V _{DS} =-5V	-160			A	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-17A		70		S	
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-15V, f=1MHz		4580	5500	pF	
Output Capacitance	C _{oss}			755			
Reverse Transfer Capacitance	C _{rss}			564			
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		160	210	Ω	
Total Gate Charge (10V)	Q _g	V _{GS} =-10V, V _{DS} =-15V, I _D =-17A		87	105	nC	
Total Gate Charge (4.5V)				41			
Gate Source Charge			Q _{gs}		12.8		
Gate Drain Charge			Q _{gd}		17		
Turn-On DelayTime	t _{d(on)}	V _{GS} =-10V, V _{DS} =-15V, R _L =0.9Ω, R _{GEN} =3Ω		180		ns	
Turn-On Rise Time	t _r			260			
Turn-Off DelayTime	t _{d(off)}			1200			
Turn-Off Fall Time	t _f			9700			
Body Diode Reverse Recovery Time	t _{rr}	I _F =-17A, di/dt=300A/us		32	40	nC	
Body Diode Reverse Recovery Charge	Q _{rr}			77			
Maximum Body-Diode Continuous Current	I _S				-3	A	
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V			-1	V	

Note :The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	4447A
	KC****

P-Channel MOSFET AO4447A (KO4447A)

■ Typical Characteristics

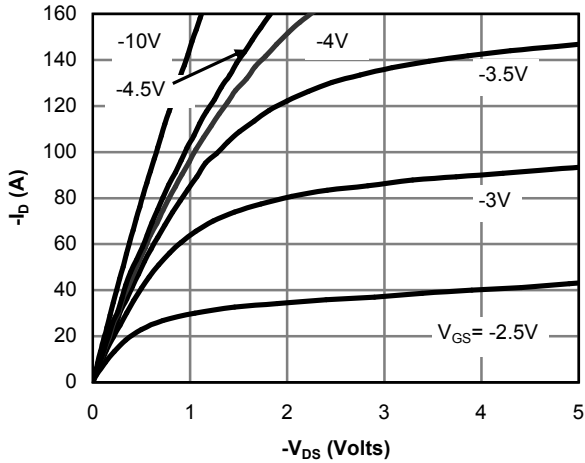


Figure 1: On-Region Characteristics(Note E)

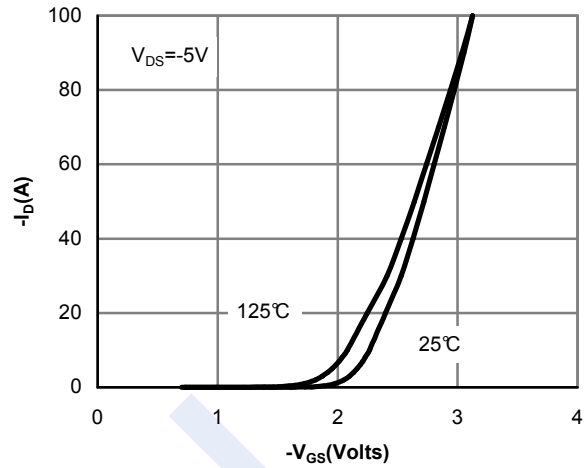


Figure 2: Transfer Characteristics(Note E)

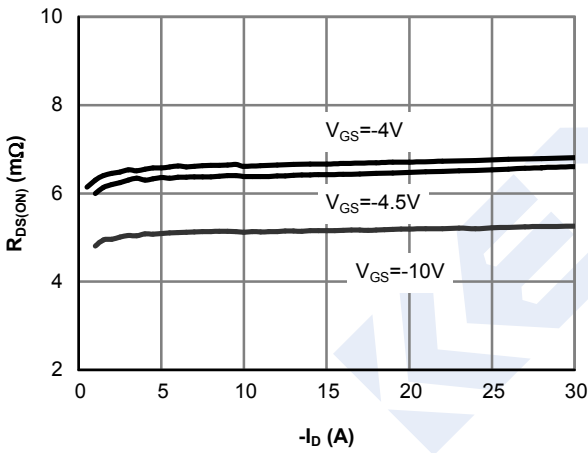


Figure 3: On-Resistance vs. Drain Current and Gate Voltage(Note E)

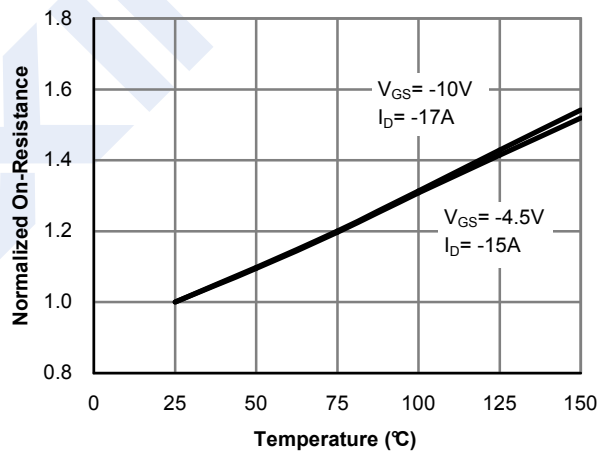


Figure 4: On-Resistance vs. Junction Temperature(Note E)

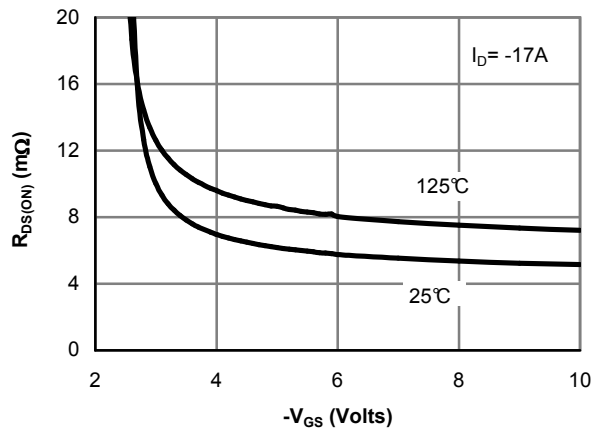


Figure 5: On-Resistance vs. Gate-Source Voltage(Note E)

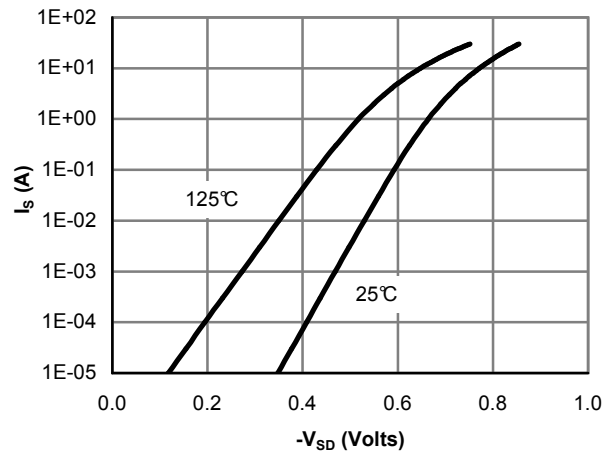


Figure 6: Body-Diode Characteristics(Note E)

P-Channel MOSFET AO4447A (KO4447A)

■ Typical Characteristics

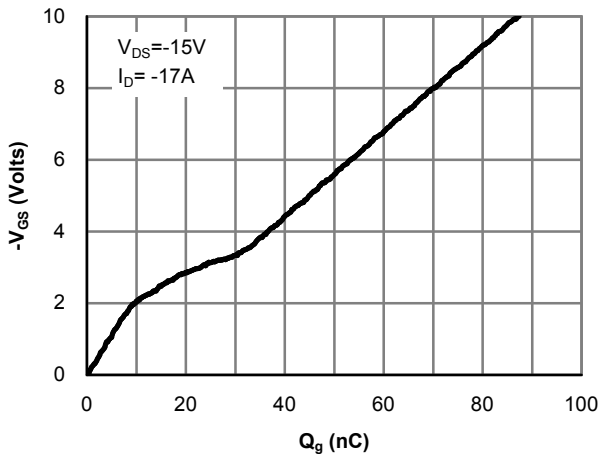


Figure 7: Gate-Charge Characteristics

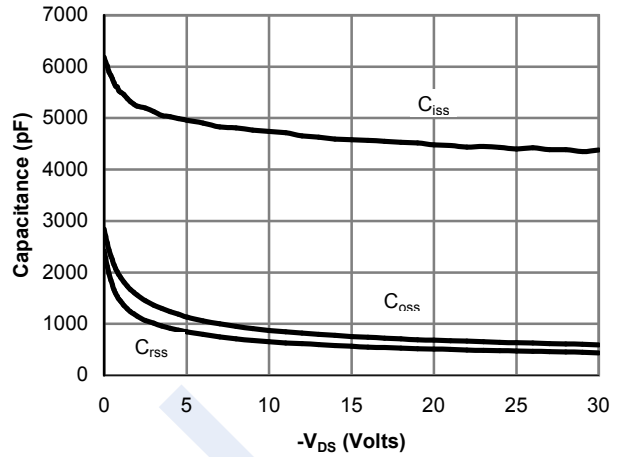


Figure 8: Capacitance Characteristics

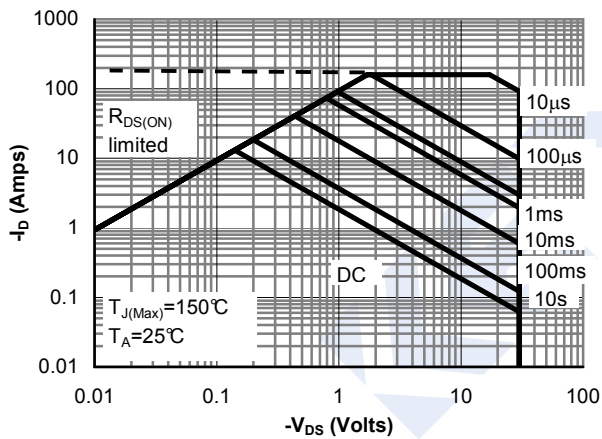


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

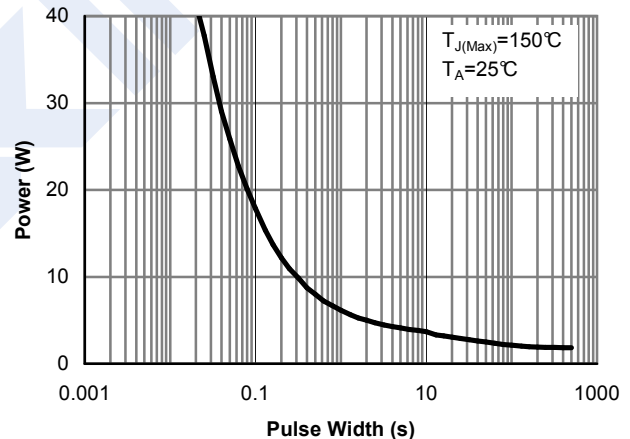


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

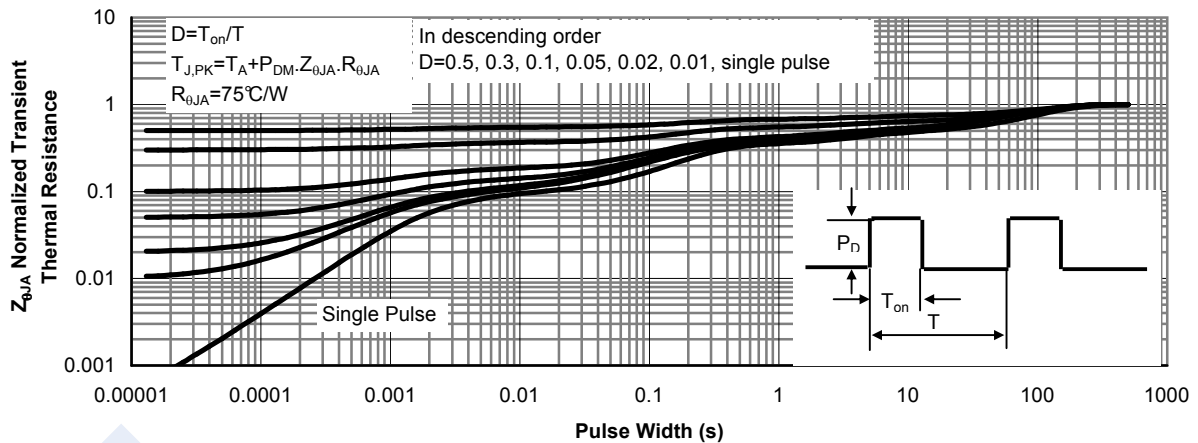


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)